

Laboratory 4: Biasing of Bipolar Transistors
Laboratory Exercises

INTRODUCTION**Objectives**

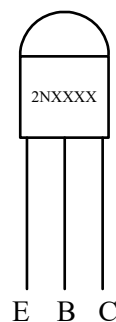
In this lab, we will design and build three different bias circuits for BJT's (Bipolar Junction Transistors). In our terminology, $\beta = \beta_{dc}$.

Summary of Procedures

- (i) Design bias circuits around transistors with typical properties of $\beta = 100$ and $V_{BE} = 0.7V$ (for npn) or $V_{EB} = 0.7V$ (for pnp).
- (ii) Build each circuit using a 2N3904, 2N2222, and a 2N3906.
- (iii) Measure the operating point of each circuit and take data sufficient to estimate β and V_{BE} .
- (iv) Use the HP 4155A/B/C to get β and β_{ac} near the bias point for each transistor used in "Circuit 3".

Materials Required

- HP 4155A/B/C (or HP 4145B) Semiconductor Parameter Analyzer



Transistor Pinout

- Proto-board
- Power Supplies
- DMM
- Assorted Resistors
- 2N2222 Transistor
- 2N3904 Transistor
- 2N3906 Transistor

PROCEDURE

Construct each of the circuits designed in the Preliminary Section using a 2N3904, 2N2222, and a 2N3906.

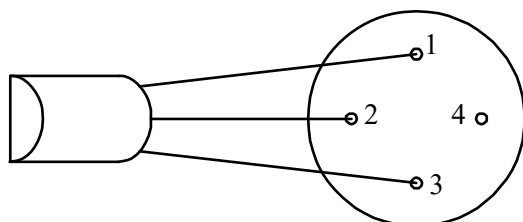
- For each circuit, evaluate the operating point (V_{CE} and I_C), being sure to use measured resistor values as needed. Record these values in the tables in the Results Sheet.
- Also take data sufficient to estimate the β of your 2N2222, 2N3904, and 2N3906. You only need to make measurements in one of the three circuits. Do not use a current meter unless you measure its internal resistance.
- Using the HP 4155A/B/C (see the procedure below), measure β and β_{ac} for your 2N2222, 2N3904, and 2N3906 **at the operating point for each transistor in Circuit 3, as measured in part (a).**

HP 4155A/B/C Instructions for Measurement of Bipolar Junction Transistor Characteristics

You will use the HP 4155A/B/C Semiconductor Parameter Analyzer to measure transistor characteristics (in this case, the common emitter current gains β and β_{ac}). Remember that you must obtain β and β_{ac} at the operating point (I_C and V_{CE}) corresponding to your results in Circuit 3.

The following procedure will make the necessary measurement and provide the required data plot. The HP 4155B has two types of keys: “hard” keys, which are dedicated buttons on the front panel, and a column of “soft” keys, just to the right of the screen. In the procedure below, a KEY is a hard key, and a KEY is a soft key. Note that you may have to use the EXTN (extension) soft key, which pages from one soft key menu to the next, to find some of the indicated soft key entries.

- I. Connect your transistor to the test fixture as shown below (same for all three transistors):




1: Emitter : SMU3/VSU1 (CONST)

2: Base : SMU2 (VAR2)

3: Collector : SMU1 (VAR1)

- II. For the npn transistors (2N3904 and 2N2222):

- (1) CHAN to navigate to the “CHANNEL DEFINITION” screen. Name the channels according to the pins above. Be sure to set V_C to VAR1 (in voltage mode) and I_B to VAR2 (in current mode), which will allow you to sweep V_{CE} while stepping I_B . The datasheets for these transistors can be found on the course website.

- (2) MEAS to get to the “SWEEP SETUP” screen. Set the sweep parameters so that V_{CE} is swept from 0V to 10V (in steps of at most 100mV) and I_B is swept from 0 to 100 μ A in 10 μ A steps. Be sure to ground V_E and set the compliances (both voltages and currents) to reasonable values given your expected bias voltages and currents.
- (3) DISPLAY to get to the “DISPLAY SETUP” screen. Here you should setup the axes to plot I_C vs. V_{CE} while stepping I_B .
- (4) GRAPH/LIST to get the “GRAPHICS PLOT” window.
- (5) SINGLE to perform the measurement.
- (6) SCALING, AUTOSCALING if necessary to view the whole plot.
- (7) MARKER/
CURSOR, MARKER
OFF to turn marker on (the soft key should now read MARKER
ON); move it to the V_{CE} you measured for circuit 3 in part (a) with the  knob.
- (8) MARKER
SKIP to move from curve to curve (different I_B 's) in the characteristic until you find the I_C value closest to the *measured* I_C for circuit 3 in part (a). β is then I_C/I_B .
- (9) If the closest value of I_C is *not* within ± 0.5 mA of your *measured* I_C , you must adjust the input values of I_B to come closer. You will do this by adjusting the starting value of I_B (originally set at 10 μ A), which will have the effect of shifting the measured characteristic up or down on the plot (depending on whether you increase or decrease, respectively, the starting value of I_B). You should change the starting value to be somewhere in the range of $5\mu\text{A} < I_B < 15\mu\text{A}$. You can come very close to the best correct value by estimating $\beta = \frac{I_C}{I_B}$ at the value of I_C that came closest to your measured I_C .
- (10) To measure β_{ac} you can use the combination of the marker and a cursor to find two different data points. Move the marker (the circle) to be at the data point corresponding to I_{B1} , I_{C1} , and V_{CE} (where V_{CE} should correspond to that obtained for the same transistor in circuit 3). Move the cursor (the cross) to be at the second data point corresponding to I_{B2} , I_{C2} (within ± 0.5 mA of the I_C measured in circuit 3), and the same V_{CE} . Then

$$\beta = \frac{I_{C2}}{I_{B2}}; \beta_{ac} = \frac{I_{C2} - I_{C1}}{I_{B2} - I_{B1}}$$

III. For the 2N3906, you should follow the same general procedure, adjusting your channel and variable assignments based on your knowledge of pnp transistors.

*Laboratory 4: Biasing of Bipolar Transistors***Results Sheet for Laboratory Exercises**

NAME: _____

LAB SECTION: _____

(a)

Values of V_{CE}

CIRCUIT	2N3906	2N3904	2N2222
1			
2			
3			

Values of I_C

CIRCUIT	2N3906	2N3904	2N2222
1			
2			
3			

(b) Values of β from circuit:

2N222 _____, 2N3904 _____, 2N3906 _____

Which circuit did you choose to make your estimation? Why?

(c) Values of β/β_{ac} from HP 4155B (attach 3 annotated HP 4155B plots)

2N222 _____ / _____, 2N3904 _____ / _____, 2N3906 _____ / _____

Briefly outline your measurements. (How were I_C , V_{CE} , and β measured and how was the HP 4155B used?)

Comment on the relative properties of each of the circuits used in this design. (Explain sensitivity to β for each circuit.)